



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

RECEIVED

AUG 21 2002

TC 2800 MAIL ROOM

#8/A
8-28-02
Mouil

In re the Application of:

Hitoshi ASADA et al.

Serial Number: 09/753,616

Group Art Unit: 2811

Filed: January 4, 2001

Examiner: Samuel A. GEBREMARIAM

For: CMOS IMAGE SENSOR AND MANUFACTURING METHOD OF THE SAME

AMENDMENT UNDER 37 CFR §1.111

Commissioner of Patents and Trademarks
Washington, D.C. 20231

August 12, 2002

Sir:

In response to the Office Action dated April 12, 2002, please amend the above-identified application as follows:

IN THE SPECIFICATION:

Please amend the specification as follows:

Please replace the paragraph beginning at page 9, line 27, with the following rewritten paragraph:

A' Next, as shown in Fig. 4B and Fig. 12B, the entire surface of the resultant structure is coated with a photoresist film 13 so as to cover the silicon nitride film 11, and an opening portion is provided at a portion corresponding to a P channel MOS transistor formation portion after exposure and developing steps. Phosphorus (P) is ion-injected to the semiconductor substrate 10 through the opening portion under conditions of, for example, 180 keV and $1.4 \times 10^{13}/\text{cm}^2$, and

A